

RoHS

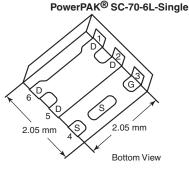
COMPLIANT

HALOGEN FREE

Vishay Siliconix

N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω) (Max.)	I _D (A) ^a	Q _g (Typ.)		
30	0.018 at V _{GS} = 10 V	12	5 nC		
	0.022 at V_{GS} = 4.5 V	12	5110		



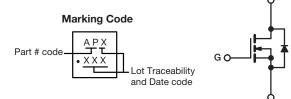
Ordering Information: SiA418DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- TrenchFET[®] Power MOSFET
- 100 % Rg Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- DC/DC Converters and Synchronous Buck Converters
 - Lower Ringing Voltage from Soft Turn-On
 - High Efficiency from Fast Turn-Off
 - Lower Shoot-Through Possibility



N-Channel MOSFET

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	30	v	
Gate-Source Voltage		V _{GS}	± 20	V	
	T _C = 25 °C		12 ^a		
Continuous Drain Current ($T_1 = 150 \ ^{\circ}C$)	T _C = 70 °C	1-	12 ^a		
	T _A = 25 °C	I _D	12 ^{a,b, c}		
	T _A = 70 °C		9.7 ^{b, c}	А	
Pulsed Drain Current (t = 300 µs)		I _{DM}	40		
Continuous Course Dusin Diada Current	T _C = 25 °C	L.	12 ^a		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	2.9 ^{b, c}		
	T _C = 25 °C		19		
Maximum Power Dissipation	T _C = 70 °C	P	12	w	
	T _A = 25 °C	P _D	3.5 ^{b, c}	vv	
	T _A = 70 °C		2.2 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{d, e}			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	28	36	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	5.3	6.5		

Notes:

a. Based on package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (www.vishav.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 80 °C/W.

Document Number: 63911 For technical questions, contact:: pmostechsupport@vishay.com

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S13-0462-Rev. C, 04-Mar-13

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V_{GS} = 0 V, I _D = 250 µA	30			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		34		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	5		- 5			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.2		2.4	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1		
		$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$			10	- μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5$ V, $V_{GS} = 10$ V	10			А	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 9 A		0.015	0.018	Ω	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 7 \text{ A}$		0.018	0.022		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 9 A		35		S	
Dynamic ^b						1	
Input Capacitance	C _{iss}			570		pF	
Output Capacitance	C _{oss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		126			
Reverse Transfer Capacitance	C _{rss}			52			
Total Gate Charge	Qg	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 12 \text{ A}$		11	17		
				5	7.5	nC	
Gate-Source Charge	Q _{gs}	V_{DS} = 15 V, V_{GS} = 4.5 V, I_{D} = 12 A		1.7			
Gate-Drain Charge	Q _{gd}			1.6			
Gate Resistance	R _g	f = 1 MHz	0.2	1	2	Ω	
Turn-On Delay Time	t _{d(on)}			5	10	- ns	
Rise Time	t _r	V_{DD} = 15 V, R_L = 1.5 Ω		10	20		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ 10 A, V_GEN = 10 V, R_g = 1 Ω		15	30		
Fall Time	t _f			10	20		
Turn-On Delay Time	t _{d(on)}			12	25		
Rise Time	t _r	V_{DD} = 15 V, R_L = 1.5 Ω		15	30		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ 10 A, V_GEN = 4.5 V, R_g = 1 Ω		15	30		
Fall Time	t _f			10	20		
Drain-Source Body Diode Characteristic	s						
Continuous Source-Drain Diode Current	۱ _S	$T_{C} = 25 \ ^{\circ}C$			12	A	
Pulse Diode Forward Current ^a	I _{SM}				40		
Body Diode Voltage	V _{SD}	I _S = 10 A		0.85	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}			20	40	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 10 A, dl/dt = 100 A/μs, T _J = 25 °C		11	20	nC	
Reverse Recovery Fall Time	t _a	$r_{\rm F} = 10$ A, $u/u_{\rm I} = 100$ A/µs, $r_{\rm J} = 25$ °C		12			
Reverse Recovery Rise Time	very Rise Time t _b			8		ns	

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

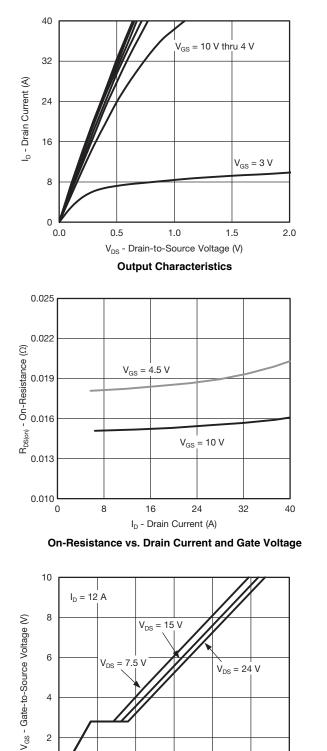
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

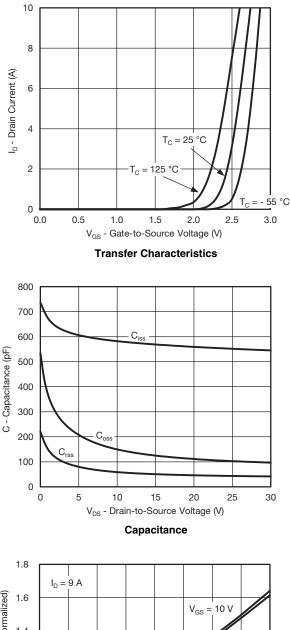
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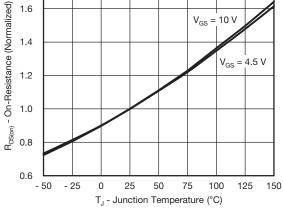


SiA418DJ Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)







On-Resistance vs. Junction Temperature

2

4

6

Q_g - Total Gate Charge (nC)

Gate Charge

8

10

12

0

0

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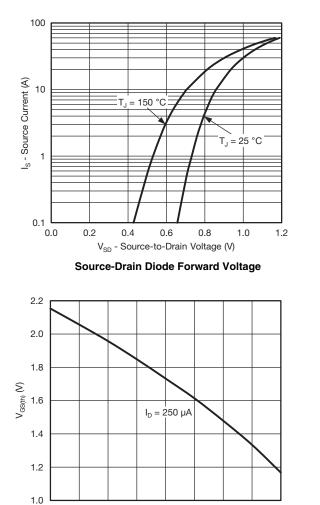
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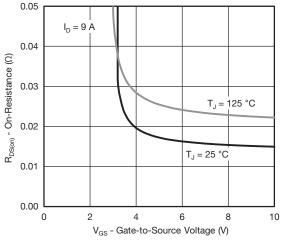
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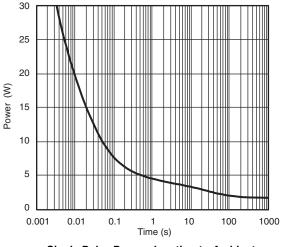
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

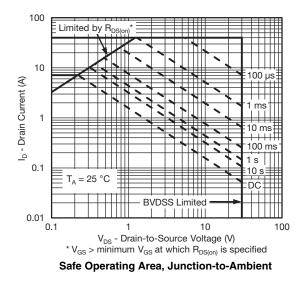




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



50 - 25

0

25

50

T_J - Temperature (°C)

Threshold Voltage

75

100

125

150

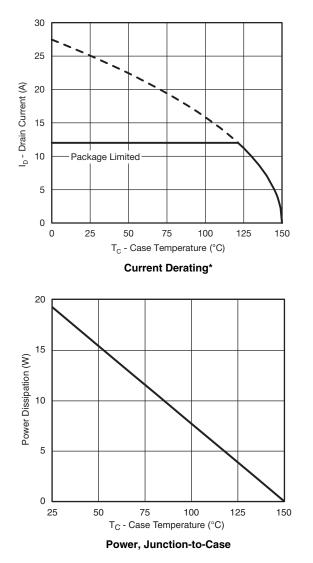
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

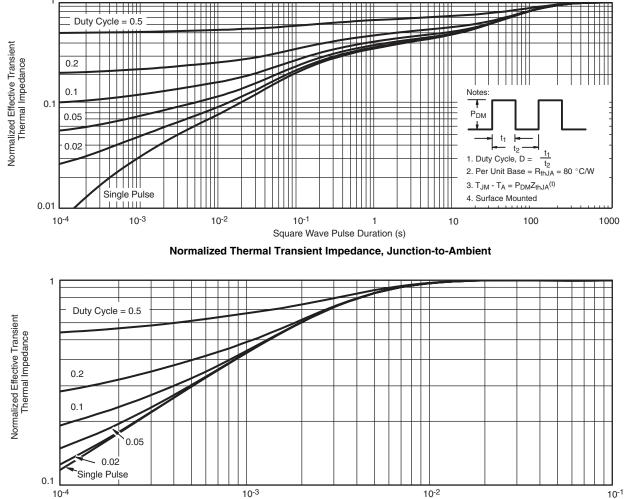


* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Square Wave Pulse Duration (s)

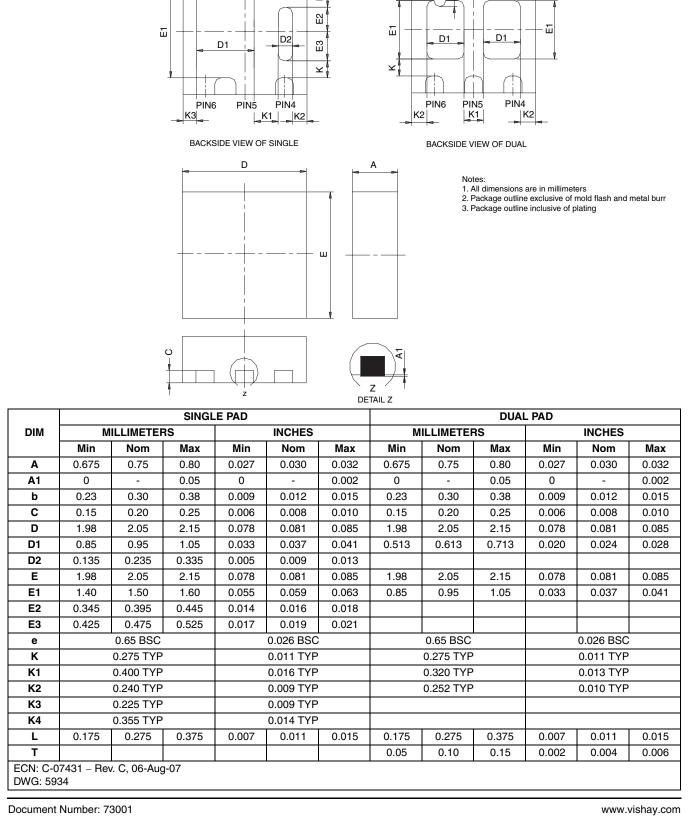
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63911.

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PowerPAK[®] SC70-6L

b PIN2 PIN1 PIN3 _ ₹

Package Information Vishay Siliconix

__ ₿

b

PIN3

PIN2

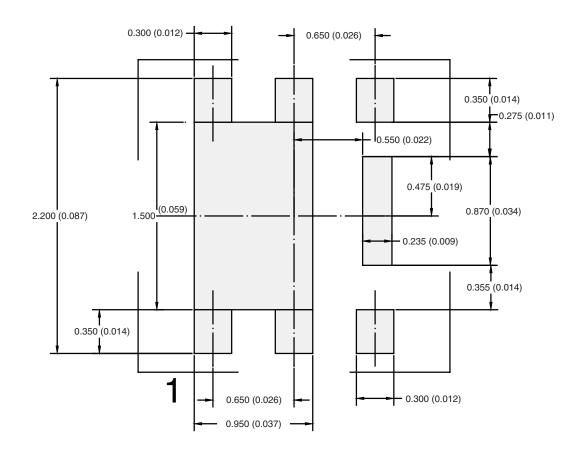
PIN1

¥

VISHA



RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC70-6L Single



Dimensions in mm/(Inches)

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